**Preferred Device** 

#### **Triacs**

#### **Silicon Bidirectional Thyristors**

Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability 150 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- Device Marking: Logo, Device Type, e.g., MAC16CD, Date Code

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
M	ge(1) AC16CD AC16CM AC16CN	VDRM, VRRM	400 600 800	Volts
On-State RMS Current (Full Cycle Sine Wave 50 to 6 T <sub>C</sub> = 80°C)	60 Hz;	I <sub>T</sub> (RMS)	16	А
Peak Non-Repetitive Surge Cur (One Full Cycle, 60 Hz, T <sub>J</sub> =		I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.33 ms)		l <sup>2</sup> t	93	A <sup>2</sup> sec
Peak Gate Power (Pulse Width ≤ 1.0 μs, T <sub>C</sub> = 8	30°C)	P <sub>GM</sub>	20	Watts
Average Gate Power (t = 8.3 ms, T <sub>C</sub> = 80°C)		P <sub>G</sub> (AV)	0.5	Watts
Operating Junction Temperature	e Range	TJ	-40 to +125	°C
Storage Temperature Range	·	T <sub>stg</sub>	-40 to +150	°C

<sup>(1)</sup> V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

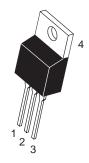


#### ON Semiconductor

http://onsemi.com

# TRIACS 16 AMPERES RMS 400 thru 800 VOLTS





TO-220AB CASE 221A STYLE 4

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

#### **ORDERING INFORMATION**

Device	Package	Shipping
MAC16CD	TO220AB	50 Units/Rail
MAC16CM	TO220AB	50 Units/Rail
MAC16CN	TO220AB	50 Units/Rail

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance  — Junction to Case  — Junction to Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

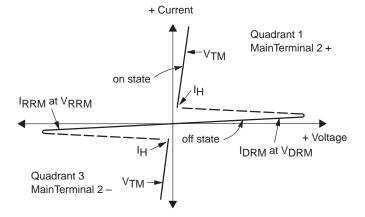
#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•	•	
Peak Repetitive Blocking Current $(V_D = Rated \ V_{DRM}, \ V_{RRM} \ Gate \ Open) \\ T_J = 25^{\circ}C \\ T_J = 125^{\circ}C$	IDRM, IRRM	_ _	_ _	0.01 2.0	mA
ON CHARACTERISTICS			•		
Peak On-State Voltage <sup>(1)</sup> (I <sub>TM</sub> = ±21 A Peak)	VTM	_	1.2	1.6	V
Gate Trigger Current (Continuous dc) $ (V_D = 12 \ V, \ R_L = 100 \ \Omega) $ $ MT2(+), \ G(+) $ $ MT2(+), \ G(-) $ $ MT2(-), \ G(-) $	IGT	8.0 8.0 8.0	12 16 20	35 35 35	mA
Holding Current (V <sub>D</sub> = 12 V, Gate Open, Initiating Current = ±150 mA)	lΗ	_	20	50	mA
Latching Current ( $V_D = 12 \text{ V}, I_G = 35 \text{ mA}$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	IL	_ _ _	25 40 24	50 80 50	mA
Gate Trigger Voltage (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) $ $ MT2(+),\ G(+) $ $ MT2(+),\ G(-) $ $ MT2(-),\ G(-) $	VGT	0.5 0.5 0.5	.75 .72 .82	1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS			•		
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dv/dt = 24 V/ $\mu$ s, Gate Open, $T_J = 125^{\circ}\text{C}$ , f = 250 Hz, $C_L = 10 \ \mu\text{F}$ , $L_L = 40 \ \text{mH}$ , with Snubber)	(di/dt) <sub>C</sub>	15	_	_	A/ms
Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, Gate Open, T <sub>J</sub> = 125°C)	dv/dt	600	_	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz	di/dt	_	_	10	A/μs

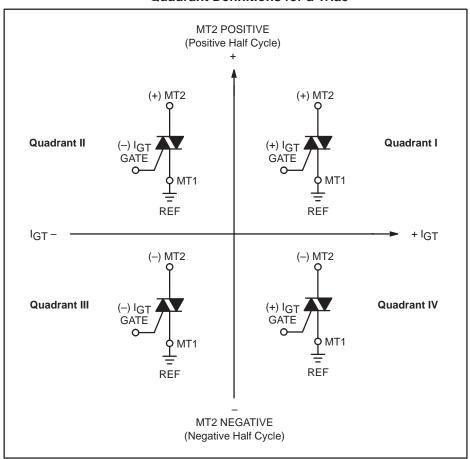
<sup>(1)</sup> Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
lΗ	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

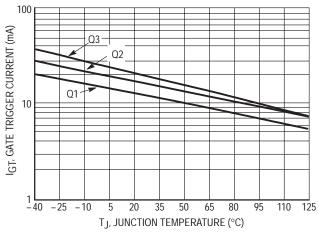


Figure 1. Typical Gate Trigger Current versus Junction Temperature

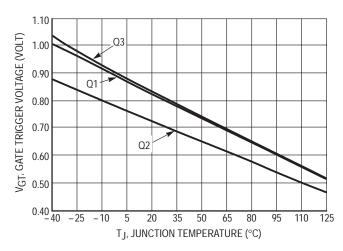


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

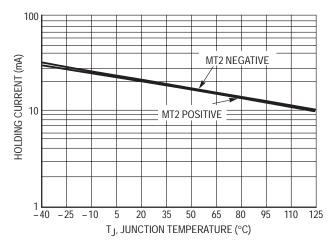


Figure 3. Typical Holding Current versus Junction Temperature

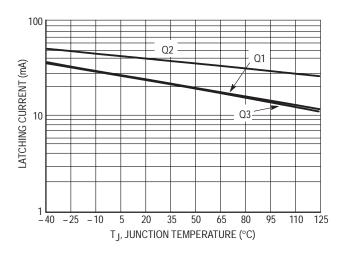


Figure 4. Typical Latching Current versus Junction Temperature

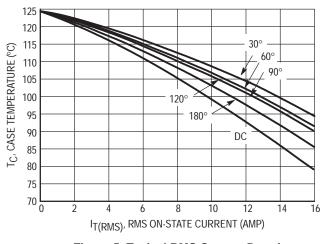


Figure 5. Typical RMS Current Derating

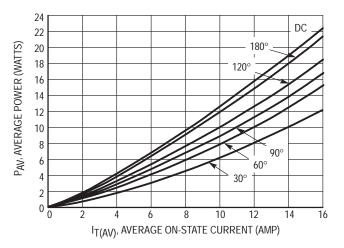


Figure 6. On-State Power Dissipation

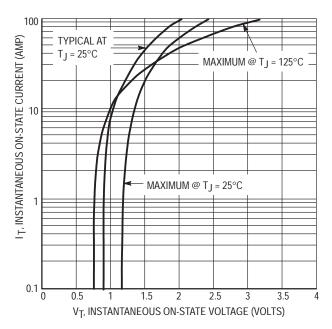


Figure 7. On-State Characteristics

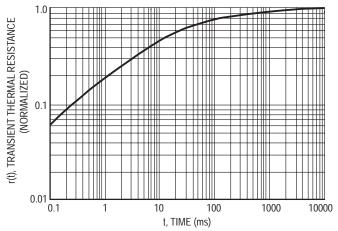
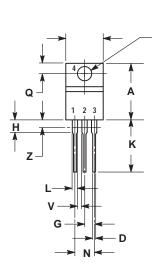
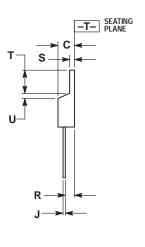


Figure 8. Typical Thermal Response

#### **PACKAGE DIMENSIONS**

#### TO-220AB CASE 221A-09 **ISSUE Z**





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2



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